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Sheet	1	of	1	Attorney Docket Number	TSM03-0556
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U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
WJH	A	US-6,258,664 B1	07-10-2001	Reinberg	
	B	US-6,358,791 B1	03-19-2002	Hsu, et al.	
	C	US-2002/0153549 A1	10-24-2002	Laibowitz, et al.	
	D	US-6,475,838 B1	11-05-2002	Bryant, et al.	
	E	US-2003/0030091 A1	02-13-2003	Bulsara, et al.	
	F	US-6,524,905 B2	02-25-2003	Yamamichi, et al.	
WJH	G	US-6,558,998 B2	05-06-2003	Belleville, et al.	
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FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ - Number ⁴ - Kind Code ⁵ (if known)				
WJH	H	WO 03/017336 A2	02-27-2003	Amberwave Systems Corporation		

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
WJH	I	WANG, L.K., et al., "On-Chip Decoupling Capacitor Design to Reduce Switching-Noise-Induced Instability in CMOS/SOI VLSI," Proceedings of the 1995 IEEE International SOI Conference, Oct. 1995, pp. 100-101.	
WJH	J	YEOH, J.C., et al., "MOS Gated Si:SiGe Quantum Wells Formed by Anodic Oxidation," Semicond. Sci. Technol. (1998), Vol. 13, pp. 1442-1445, IOP Publishing Ltd., UK.	
WJH	K	CAVASSILAS, N., et al., "Capacitance-Voltage Characteristics of Metal-Oxide-Strained Semiconductor Si/SiGe Heterostructures," Nanotech 2002, Vol. 1, pp. 600-603.	

Examiner Signature	Date Considered	
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